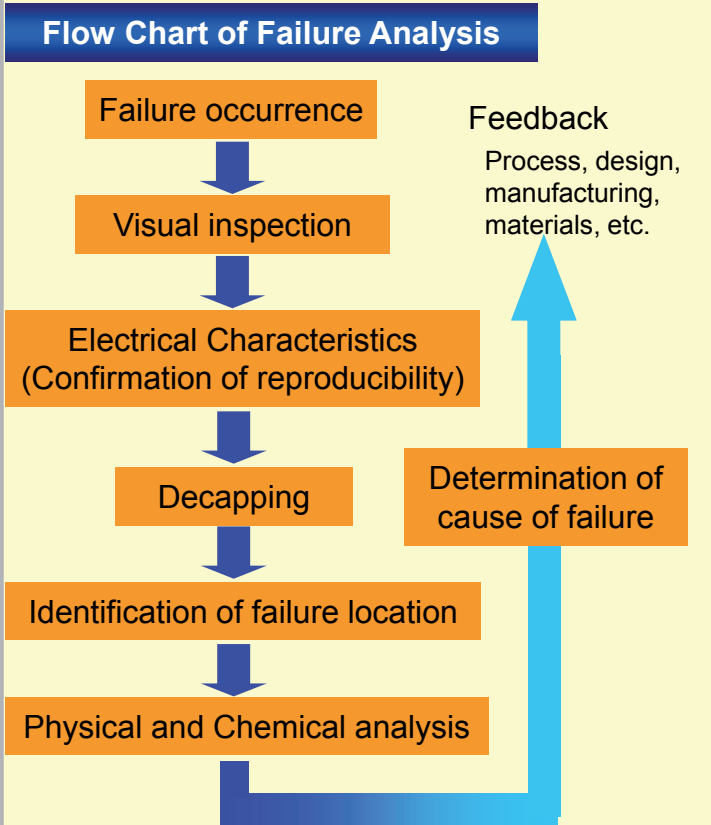


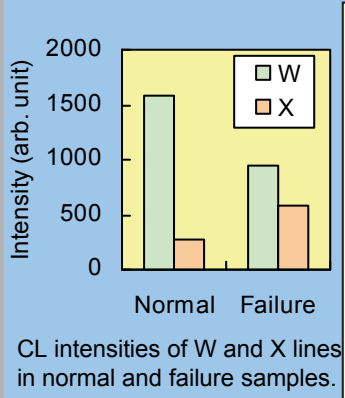
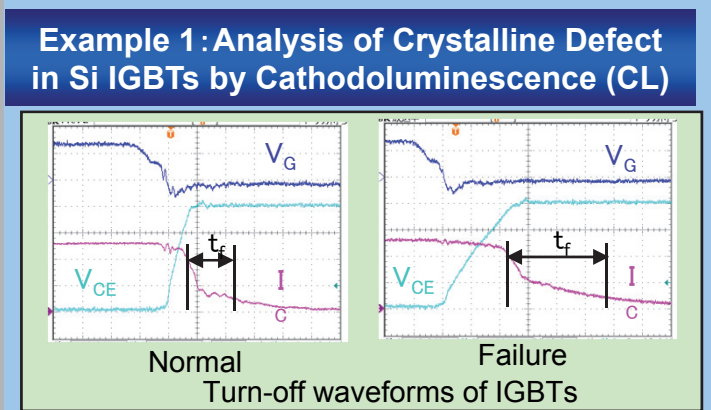
Failure Analysis Techniques for Semiconductor Devices

Physical and chemical analysis techniques are widely used for semiconductor failure analysis. The analysis of "invisible defects" is becoming important because of the requirement of high-level reliability.

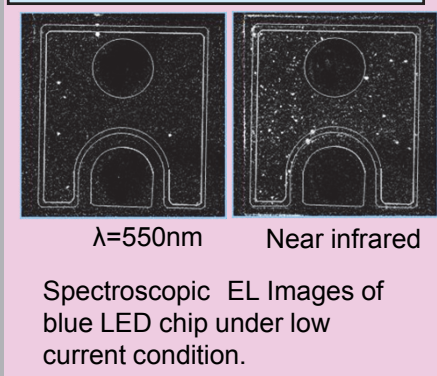
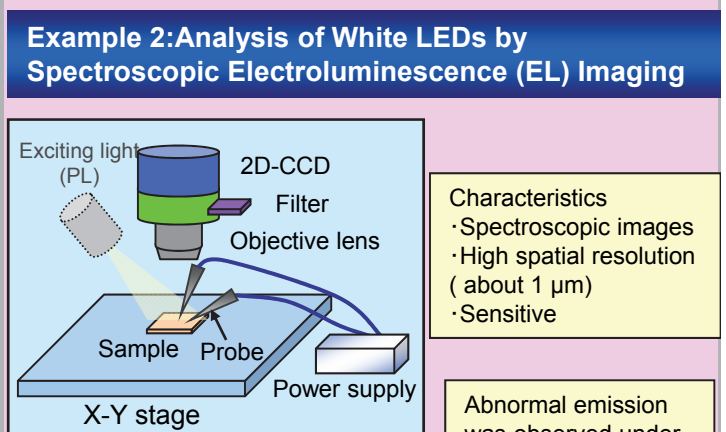


Techniques used in Failure Analysis

Identification of Defective Region Package: Scanning acoustic tomographs (SAT), X-ray, X-ray CT, Thermal emission microscope, etc. Chip: Photo emission microscope, OBIRCH, Voltage contrast, etc. (Some methods are done with outsourcing.)
Physical and Chemical analysis Morphological study: TEM, EDX/EELS, SEM, EBSD Surface analysis: SIMS, TOF-SIMS, XPS, AES, EPMA, RBS/HFS, AFM/SSRM/SCM Structural analysis: FT-IR, Raman, PL, CL, ESR, XRD, GIXR, EXAFS, NMR Organic and inorganic analysis: GC·GC/MS, LC/MS, NMR, GPC, ICP-AES, ICP-MS, XRF, IC Materials Characterization: Mechanical and rheological properties, Thermophysical properties, Thermal analysis, DSC, TG-MS/TPD-MS



CL measurements were done on the cross-section of IGBTs. Point defects were remarkably changed. The tetra-interstitials (X) were increased and the tri-interstitials (W) were decreased in the failure sample. We consider that the minority carrier lifetime in the failure sample is elongated by the decrease of total number of defects by the agglomeration of interstitials.



Characteristics

- Spectroscopic images
- High spatial resolution (about 1 μm)
- Sensitive

Abnormal emission was observed under low current condition. The wavelength of the abnormal emission was near-infrared region or about 550 nm. We consider that the cause of abnormal emission can be categorized by the wavelength nondestructively.